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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/701,476	11/06/2003	Keiji Fujita	04329.3172	8591
75	7590 10/06/2004		EXAMINER	
Finnegan, Henderson, Farabow,			PHAM, THANHHA S	
Garrett & Dunn			ART UNIT	PAPER NUMBER
1300 I Street, N.W.			ARTONII	PAPER NUMBER
Washington, DC 20005-3315			2813	

DATE MAILED: 10/06/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	
	10/701,476	FUJITA ET AL.	
Office Action Summary	Examiner	Art Unit	
	Thanhha Pham	2813	
The MAILING DATE of this communication a Period for Reply	appears on the cover sheet w	ith the correspondence address	5
A SHORTENED STATUTORY PERIOD FOR REF THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a - If NO period for reply is specified above, the maximum statutory peri - Failure to reply within the set or extended period for reply will, by star Any reply received by the Office later than three months after the may earned patent term adjustment. See 37 CFR 1.704(b).	N. 1.136(a). In no event, however, may a reply within the statutory minimum of thir od will apply and will expire SIX (6) MON tute, cause the application to become Al	eply be timely filed ty (30) days will be considered timely. ITHS from the mailing date of this commun BANDONED (35 U.S.C. § 133).	nication.
Status			
1) Responsive to communication(s) filed on 17	March 2004.		
2a) This action is FINAL . 2b) T	his action is non-final.		
3) Since this application is in condition for allow closed in accordance with the practice under the condition of the cond	•	• •	its is
Disposition of Claims			
4) ☐ Claim(s) 1-20 is/are pending in the applicating 4a) Of the above claim(s) is/are withd 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) 1-20 are subject to restriction and/or	rawn from consideration.		
Application Papers			
9)☐ The specification is objected to by the Exam	iner.		
10)☐ The drawing(s) filed on is/are: a)☐ a	•		
Applicant may not request that any objection to the		• •	
Replacement drawing sheet(s) including the corr	•	· · · · · · · · · · · · · · · · · · ·	• •
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for forei a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the p application from the International Bure * See the attached detailed Office action for a l	ents have been received. ents have been received in A rionty documents have been eau (PCT Rule 17.2(a)).	pplication No received in this National Stag	l e
Attachment(s)	∆ □ 1=4== 1== 1	20mman (DTO 442)	
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 Paper No(s)/Mail Date 	Paper No(Summary (PTO-413) s)/Mail Date nformal Patent Application (PTO-152) 	

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DETAILED ACTION

Election/Restrictions

- 1. Restriction to one of the following inventions is required under 35 U.S.C. 121:
 - Claims 1-9, drawn to a semiconductor device, classified in class 257, subclass 758.
 - Species la, drawn to a semiconductor device comprising a porous insulating film formed above the semiconductor substrate, said porous insulating film have a relative dielectric constant of 2.5 or less and including a first insulating material, at least a portion of pores in the porous insulating film having on the inner wall thereof a layer of a second insulating material which differs in nature from said first insulating material.
 - Species Ib, drawn to a semiconductor device comprising
 comprising a porous insulating film formed above the
 semiconductor substrate, said porous insulating film have a relative
 dielectric constant of 2.5 or less, an average diameter of pores in
 said porous insulating film being smaller in a surface region of said
 porous insulating film than in an inner region of said porous
 insulating film.
 - II. Claim 10-20, drawn to a method for manufacturing a semiconductor device, classified in class 438, subclass 622.

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- Species IIa, drawn to a method for manufacturing a seniconductor device comprising wherein prior to filling the recessed portion with the conductive material, said porous insulating film is placed inside a chamber to expose said porous insulating film to an oxidizing gas flow and a reducing gas flow which have been alternately introduced into the chamber, to take place an oxidation-reduction reaction in said porous insulating film, thereby forming a layer of reaction product on the inner walls of pores of said porous insulating film.
- Species IIb, drawn to a method for manufacturing a seniconductor device comprising wherein the porous insulating film is irradiated with electron beam to enlarge the size of pores of the porous insulating film.

The inventions are distinct, each from the other because of the following reasons: Inventions I and II are related as process of making and product made. The inventions are distinct if either or both of the following can be shown: (1) that the process as claimed can be used to make other and materially different product or (2) that the product as claimed can be made by another and materially different process (MPEP § 806.05(f)). In the instant case, the product invention I structure can be made by another and materially different process. For example, a plug and/or wiring layer buried in the porous insulating film can be formed by providing a plug and/or wiring layer instead of

forming a recess portion on a surface of the porous insulating film then filling the recessed portion with a conductive material to form the plug and/or a wiring layer.

Because these inventions are distinct for the reasons given above and have acquired a separate status in the art as shown by their different classification, restriction for examination purposes as indicated is proper.

Because these inventions are distinct for the reasons given above and the search required for Group I is not required for Group II, restriction for examination purposes as indicated is proper.

Because these inventions are distinct for the reasons given above and have acquired a separate status in the art because of their recognized divergent subject matter, restriction for examination purposes as indicated is proper.

- 2. The product invention I of this application contains claims directed to the following patentably distinct species of the claimed invention:
 - Ia. Species Ia, drawn to a semiconductor device comprising a porous insulating film formed above the semiconductor substrate, said porous insulating film have a relative dielectric constant of 2.5 or less and including a first insulating material, at least a portion of pores in the porous insulating film having on the inner wall thereof a layer of a second insulating material which differs in nature from said first insulating material. It appears that claims 1-5 read on species Ia.
 - Ib. Species lb, drawn to a semiconductor device comprising comprising a porous insulating film formed above the semiconductor substrate, said porous

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insulating film have a relative dielectric constant of 2.5 or less, an average diameter of pores in said porous insulating film being smaller in a surface region of said porous insulating film than in an inner region of said porous insulating film. It appears that claims 6-9 read on species lb.

The product invention II of this application contains claims directed to the following patentably distinct species of the claimed invention:

- IIa. Species IIa, drawn to a method for manufacturing a seniconductor device comprising wherein prior to filling the recessed portion with the conductive material, said porous insulating film is placed inside a chamber to expose said porous insulating film to an oxidizing gas flow and a reducing gas flow which have been alternately introduced into the chamber, to take place an oxidation-reduction reaction in said porous insulating film, thereby forming a layer of reaction product on the inner walls of pores of said porous insulating film. It appears that claims 10-16 read on species IIa.
- Ilb. Species Ilb, drawn to a method for manufacturing a seniconductor device comprising wherein the porous insulating film is irradiated with electron beam to enlarge the size of pores of the porous insulating film. It appears that claims 17-20 read on species Ilb.

Applicant is required under 35 U.S.C. 121 to elect a single disclosed species for prosecution on the merits to which the claims shall be restricted if no generic claim is finally held to be allowable. Currently, no claim is generic.

Applicant is advised that a reply to this requirement must include an identification

of the species that is elected consonant with this requirement, and a listing of all claims

readable thereon, including any claims subsequently added. An argument that a claim

is allowable or that all claims are generic is considered nonresponsive unless

accompanied by an election.

elected species. MPEP § 809.02(a).

Upon the allowance of a generic claim, applicant will be entitled to consideration of claims to additional species which are written in dependent form or otherwise include all the limitations of an allowed generic claim as provided by 37 CFR 1.141. If claims are added after the election, applicant must indicate which are readable upon the

Should applicant traverse on the ground that the species are not patentably distinct, applicant should submit evidence or identify such evidence now of record showing the species to be obvious variants or clearly admit on the record that this is the case. In either instance, if the examiner finds one of the inventions unpatentable over the prior art, the evidence or admission may be used in a rejection under 35.

U.S.C. 103(a) of the other invention.

3. A telephone call was made to Richard Burgujan on 08/18/04 to request an oral election to the above restriction requirement, but did not result in an election being made.

Applicant is advised that the reply to this requirement to be complete must include an election of the invention to be examined even though the requirement be traversed (37 CFR 1.143).

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4. Applicant is reminded that upon the cancellation of claims to a non-elected invention, the inventorship must be amended in compliance with 37 CFR 1.48(b) if one or more of the currently named inventors is no longer an inventor of at least one claim remaining in the application. Any amendment of inventorship must be accompanied by a request under 37 CFR 1.48(b) and by the fee required under 37 CFR 1.17(i).

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5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanhha Pham whose telephone number is (571) 272-1696. The examiner can normally be reached on Monday and Thursday 9:00AM - 9:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Thanhha Pham Patent Examiner

Patent Examining Group 2800